

NTE569 Silicon Rectifier Fast Switching, Soft Recovery

Features:

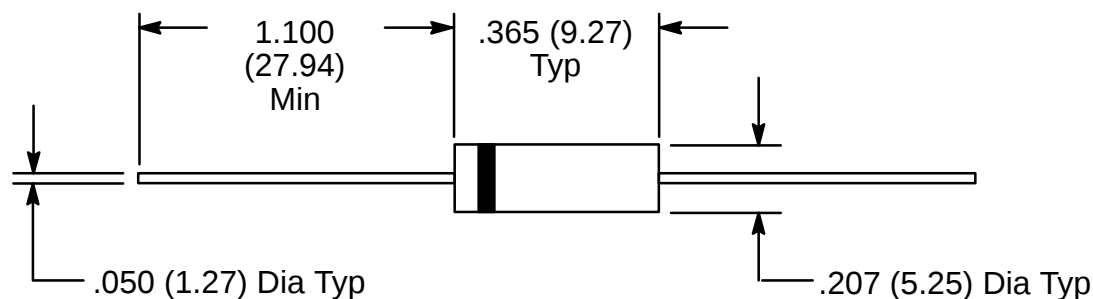
- Fast Recovery
- Diffused Junction
- High Surge Capability

Absolute Maximum Ratings:

Peak Recurrent and Non-Recurrent Reverse Voltage, V_{RRM}	600V
Forward Current (R Load, $T_A = +50^\circ\text{C}$), $I_{F(AV)}$	3A
Recurrent Peak Forward Current, I_{FRM}	15A
Peak Forward Surge Current (10ms, $T_A = +25^\circ\text{C}$), I_{FSM}	100A
Maximum Reverse Recovery Time ($I_F = 0.5\text{A}$ to $I_R = 1\text{A}$ with $I_{rr} = 0.25\text{A}$), t_{rr}	250ns
Maximum Operating Junction Temperature T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$
Lead Temperature (During Soldering, 4mm from case, 3.5sec), T_L	$+350^\circ\text{C}$
Maximum Thermal Resistance, Junction-to-Case, R_{thJC}	30°C/W

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Forward Voltage Drop	V_F	$I_F = 3\text{A}$	—	—	1.3	V
Maximum Reverse Current	I_R	$V_{RRM} = 600\text{V}$	—	—	10	μA



Color Band Denotes Cathode